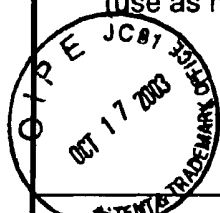


PTO/SB/08A			<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)			Application Number	10/615,127
			Filing Date	July 24, 2003
			Confirmation Number	8157
			First Named Inventor	Falster et al
			Group Art Unit	1765
			Examiner Name	H. Jeshen
			Attorney Docket No.	MEMC TP-01-2450 (3009)
Sheet	1	of	4	



U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code <sup>2</sup> (if known)		
F.H.	1	4,314,595		Yamamoto et al	02/09/1982
	2	4,376,657		Nagasawa et al	03/15/1983
	3	4,437,922		Bischoff et al	03/20/1984
	4	4,851,358		Huber	07/25/1989
	5	4,868,133		Huber	09/19/1989
	6	5,327,007		Imura et al	07/05/1994
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	8	5,403,406		Falster et al	04/04/1995
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	10	5,502,010		Nadahara et al	03/26/1996
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	13	5,561,316		Fellner	10/01/1996
	14	5,593,494		Falster	01/14/1997
	15	5,611,855		Wijaranakula	03/18/1997
F.H.	16	5,674,756		Sato et al	10/07/1997
Examiner Signature	H. Jeshen		Date Considered	1/4/04	

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		Group Art Unit	1745
		Examiner Name	Hiteshew
Sheet 2 of 4	Attorney Docket No.	MEMC TP-01-2450 (3009)	

F.H.	17	5,738,942		Kubota et al	04/14/1998
↑	18	5,788,763		Hayashi et al	08/04/1998
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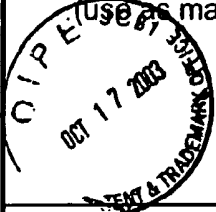
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T <sup>6</sup>
		Office	Number <sup>4</sup>	Kind Code <sup>2</sup> (if known)			
F.H.	25	DE	43 23 964	A1	Nadahara et al	01/20/1994	
↑	26	EP	0 503 816	A1	Fusegawa et al	09/16/1992	
	27	EP	0 536 958	A1	Otakawa et al	04/14/1993	
	28	EP	0 954 018	A1	Sadamitsu et al	11/03/1999	
	29	EP	0 964 435	A1	Takeno et al	12/15/1999	
↓	30	JP	5155700		Atsushi et al	06/22/1993	A
F.H.	31	JP	7201874		Hirochika	08/04/1995	A

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		Examiner Name	Hiteshen		
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F.H.	32	JP	7321120		Shiro et al	12/08/1995	A
↑	33	JP	7335657		Masahiko	12/12/1995	A
	34	JP	8045944		Takashi et al	02/16/1996	A
	35	JP	8045945		Yuhki et al	02/16/1996	A
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	37	JP	11067781		Nobuyuki et al	03/09/1999	A
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F.H.	40	WO	98/45507		Falster et al	10/15/1998	

#### OTHER ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
F.H.	41	FALSTER, R., et al, The Engineering of Silicon Wafer Material Properties Through Vacancy Concentration Profile Control and the Achievement of Ideal Oxygen Precipitation Behavior, Mat. Res. Soc. Symp. Proc., vol. 510, 1998, p. 27-35	
↑	42	HARA, A., et al, Enhancement of Oxygen Precipitation in Quenched Czochralski Silicon Crystals, Journal of Applied Phys., Vol. 66, 1989, p. 3958-3960	
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Examiner Signature	<i>J. Hiteshen</i>	Date Considered	1/4/04
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		First Named Inventor	Falster et al		
		Group Art Unit	1765		
		Examiner Name	H. Yeshaw		
Sheet	4	of	4	Attorney Docket No.	MEMC TP-01-2450 (3009)

FH	45	JACOB, M., et al, Influence of TRP on Vacancy Concentrations, Mat. REs. Soc. Symp. Proc., Vol. 490, 1998, p. 129-134	
↑	46	NADAHARA, S., et al, Hydrogen Annealed Silicon Wafer, Solid State Phenomena, Vols. 57-58, 1997, p. 19-26	
	47	PAGANI, M., et al, Spatial Variations in Oxygen Precipitation in Silicon After High Temperature Rapid Thermal Annealing, Appl. Phys. Lett., Vol. 70, No. 12, 1997, p. 1572-1574	
↓	48	SHIMIZU, H., et al, Effects of Surface Defects (COPs) On Isolation Leakage and Gate Oxide Integrity in MOS Large-Scale-Integrated-Circuit Devices and Cost Effective p-lpEpitaxial Wafers, Electrochemical Society Proceedings, Vol. 99, No. 1, p. 315-323 (from a presentation on or about May 3, 1999)	
↓	40	SHIMIZU, H., et al., Excellence of Gate Oxide Integrity in Metal-Oxide-Semiconductor Large-Scale-Integrated Circuits Based on P-/P-Thin-Film Epitaxial Silicon Wafers, Jpn. J. Appl. Phys., Vol. 36, Part 1, No. 5A, 1997, p. 2565-2570	
FH	50	SHIMURA, F., Semiconductor Silicon Crystal Technology, Academic Press, Inc., San Diego, CA, 1989, p. 361-377	

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